

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Akifumi KAMIJIMA; Hisayoshi WATANABE

Application No.: New U.S. Patent Application

Filed: October 1, 2001

Docket No.: 110735

For: A METHOD FOR FABRICATING A RESIST PATTERN, A METHOD FOR PATTERNING A THIN FILM AND A METHOD FOR MANUFACTURING A MICRO DEVICE

PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 3, 6, 10, 13, 16, 19, 20, 23, 26, 29, 30, 33, 36, 39, 40, 43, 44 and 46 as follows:

3. (Amended) A fabricating method as defined in claim 1, wherein the pre-resist pattern and the resist pattern is composed of a photoresist layer as a top layer and a polymethylglutarimide layer as a bottom layer.

6. (Amended) A fabricating method as defined in claim 1, wherein the pre-resist pattern and the resist pattern is made of a picture reversion type photoresist which is made by adding a negative working agent to a positive type photoresist including a mixture of alkaline soluble phenol resin and naphthoquinonediazido.

10. (Amended) A fabricating method as defined in claim 1, wherein the pre-resist pattern and the resist pattern is made of a novolac type positive photoresist containing an additive phenol dissolution accelerator.

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